

Electronics Supplementary Information

Non-volatile organic ferroelectric memory transistor using rigid polyimide islands on elastomer substrate

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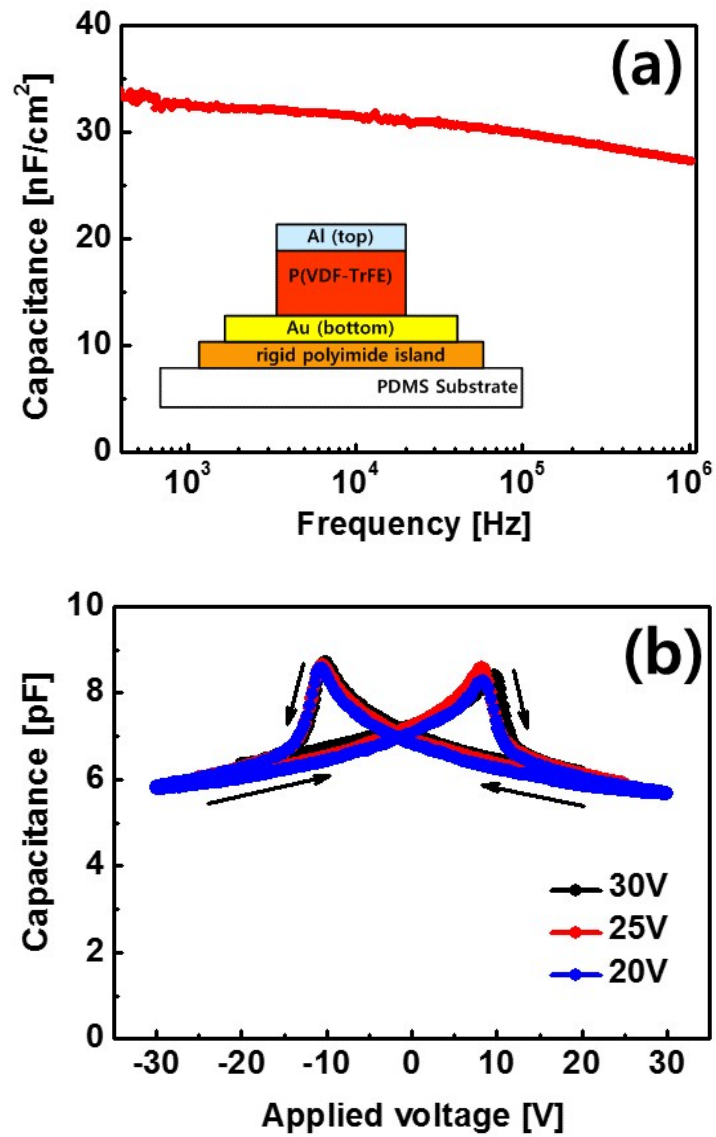


Figure S1. (a) Capacitance–frequency and (b) capacitance–voltage characteristics of the P(VDF-TrFE) capacitor fabricated on a rigid polyimide/PDMS substrate.

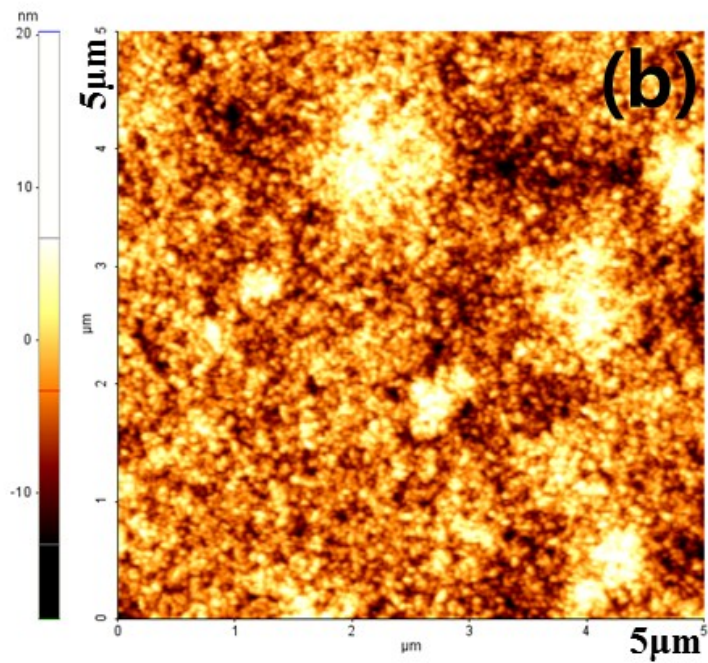
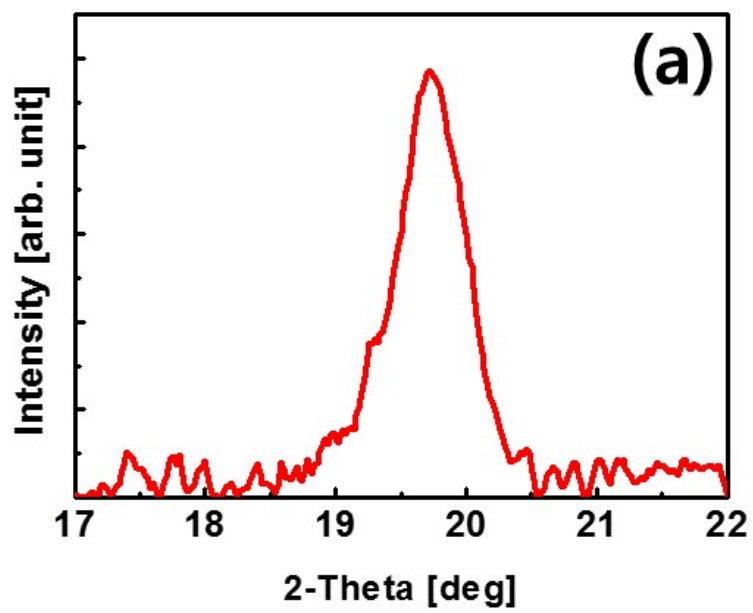


Figure S2. (a) X-ray diffraction (XRD) patterns, and (b) atomic force microscopy (AFM) image of the P(VDF-TrFE) thin film on rigid polyimide islands on elastomer substrate.

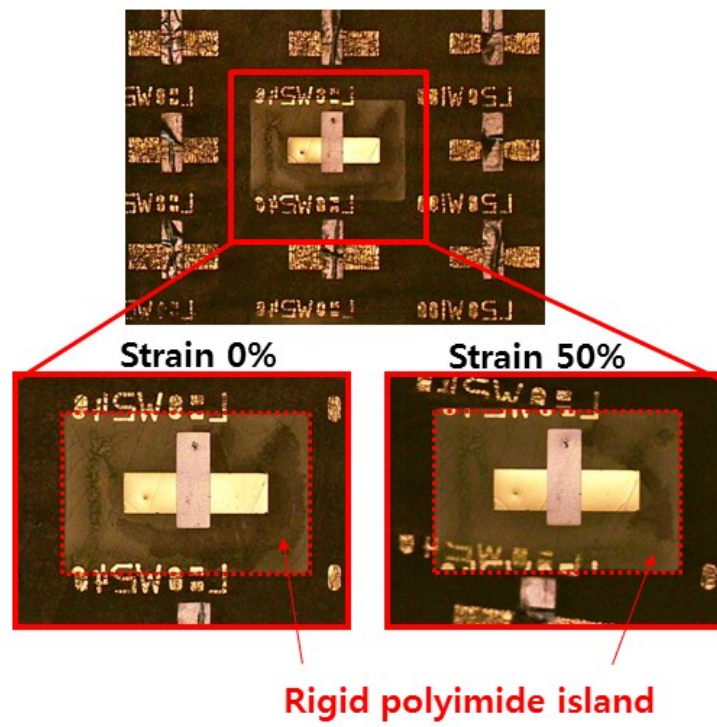


Figure S3. Optical images of uniaxially stretched OFMTs at strains of 0% and 50%.

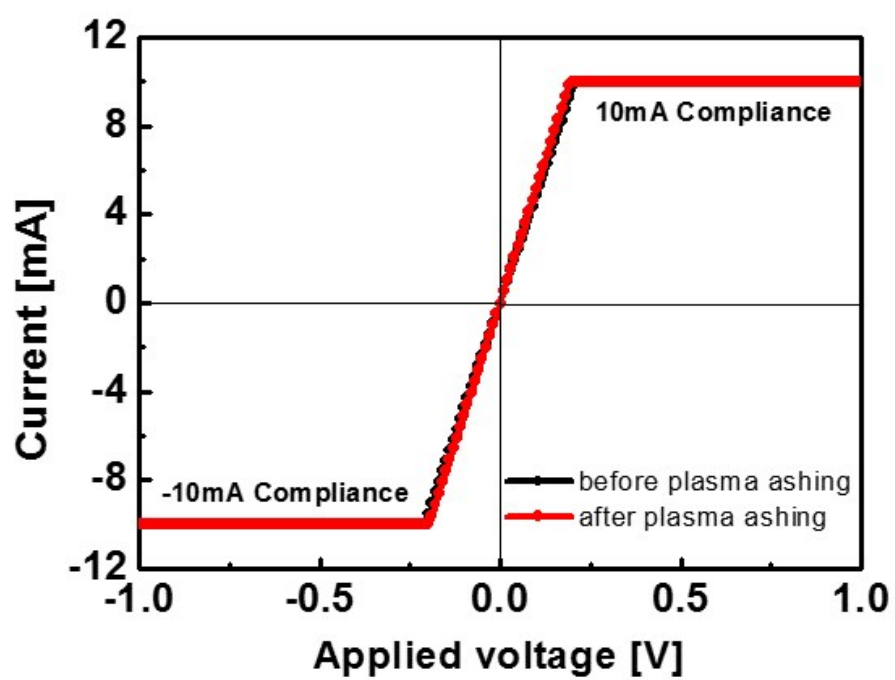


Figure S4. Current–voltage characteristics of the Al gate electrode of the OFMT fabricated on a rigid polyimide/PDMS substrate.

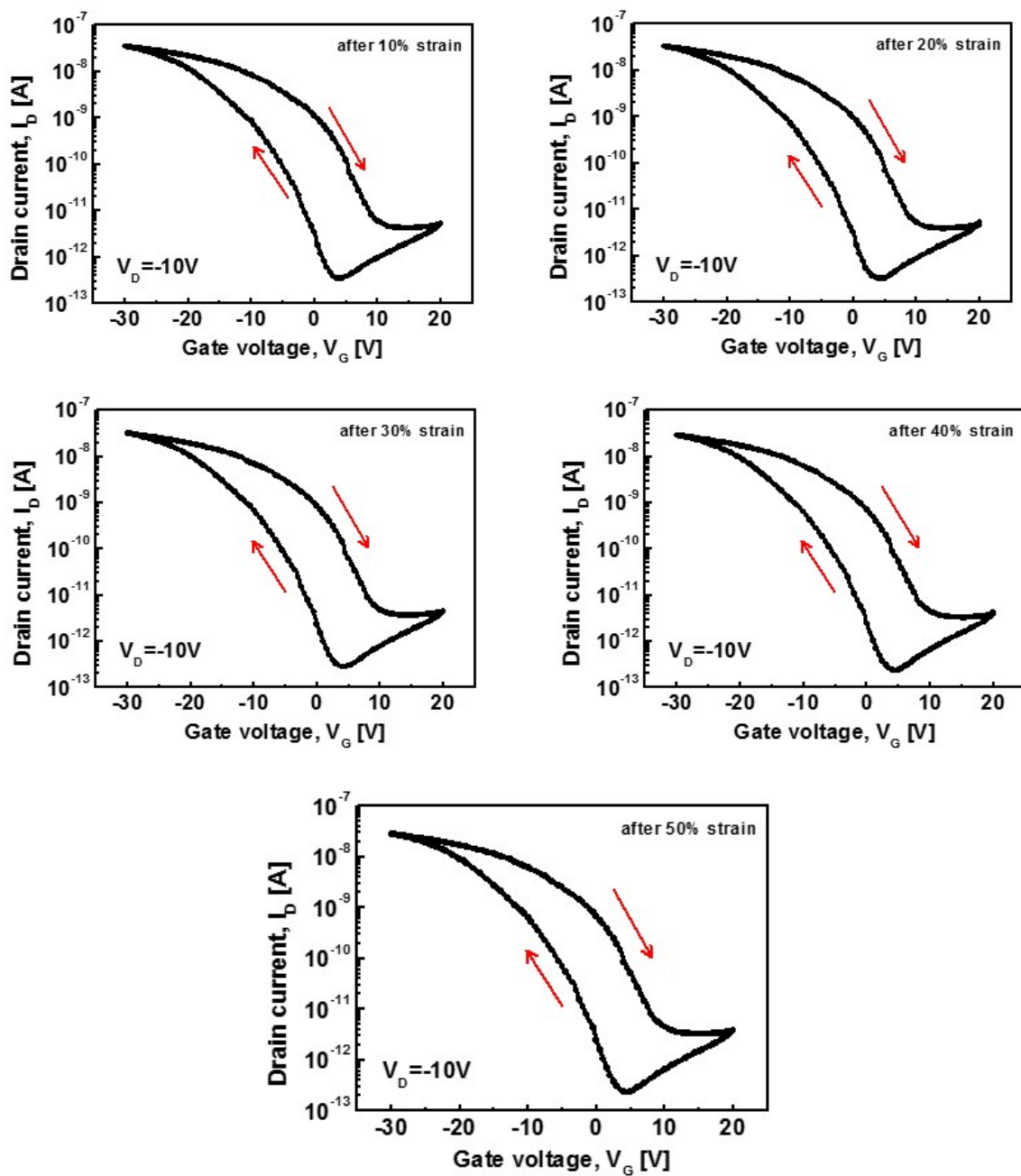


Figure S5. Transfer curves after the stretch.

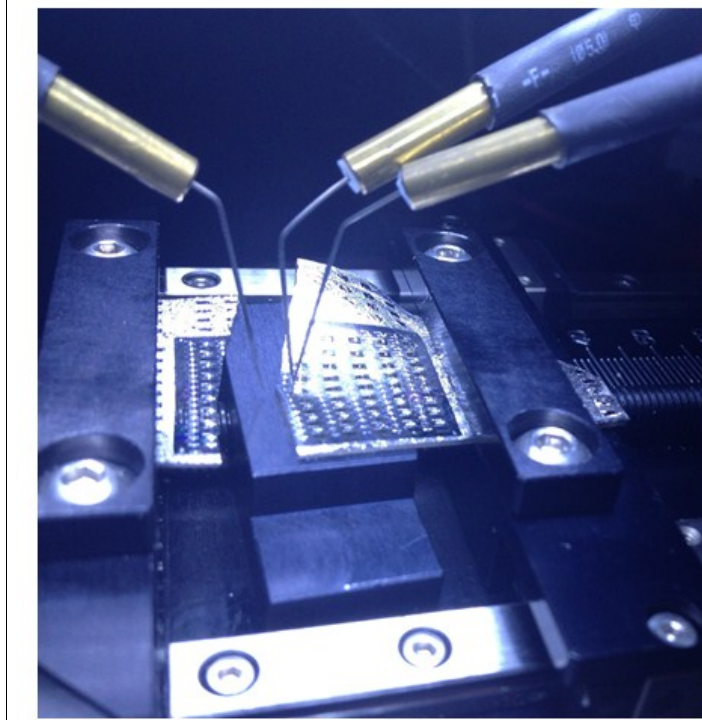


Figure S6. Optical image of uniaxially stretched OFMTs at strain of 55%.